

## N-Channel 45 V (D-S) MOSFET

### PRODUCT SUMMARY

V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A) <sup>a, e</sup>	Q <sub>g</sub> (Typ.)
45	0.0008 at V <sub>GS</sub> = 10 V	230	110 nC
	0.0012 at V <sub>GS</sub> = 4.5 V	170	

### FEATURES

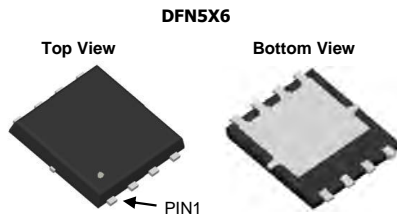
- DT-Trench Power MOSFET
- 100 % R<sub>g</sub> and UIS Tested



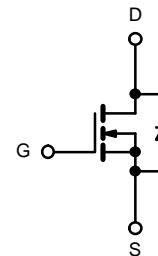
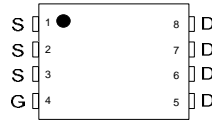
RoHS  
COMPLIANT

### APPLICATIONS

- Notebook PC Core
- VRM/POL



Top View



N-Channel MOSFET

### ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	45	V
Gate-Source Voltage	V <sub>GS</sub>	± 20	
Continuous Drain Current (T <sub>J</sub> = 175 °C)	I <sub>D</sub>	T <sub>C</sub> = 25 °C	230 <sup>a, e</sup>
		T <sub>C</sub> = 70 °C	190 <sup>e</sup>
		T <sub>A</sub> = 25 °C	52 <sup>b, c</sup>
		T <sub>A</sub> = 70 °C	38.2 <sup>b, c</sup>
Pulsed Drain Current	I <sub>DM</sub>	820	A
Avalanche Current Pulse	I <sub>AS</sub>	79	
Single Pulse Avalanche Energy		E <sub>AS</sub>	
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C	230 <sup>a, e</sup>
		T <sub>A</sub> = 25 °C	13.6 <sup>b, c</sup>
Maximum Power Dissipation	P <sub>D</sub>	T <sub>C</sub> = 25 °C	320 <sup>a</sup>
		T <sub>C</sub> = 70 °C	224
		T <sub>A</sub> = 25 °C	8.15 <sup>b, c</sup>
		T <sub>A</sub> = 70 °C	5.71 <sup>b, c</sup>
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 175	°C

### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>b, d</sup>	R <sub>thJA</sub>	10	13	°C/W
Maximum Junction-to-Case	R <sub>thJC</sub>	0.35	0.5	

Notes:

a. Based on T<sub>C</sub> = 25 °C.

b. Surface mounted on 1" x 1" FR4 board.

c. t = 10 s.

d. Calculated based on maximum junction temperature. Package limitation current is 180 A.

**SPECIFICATIONS** ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)

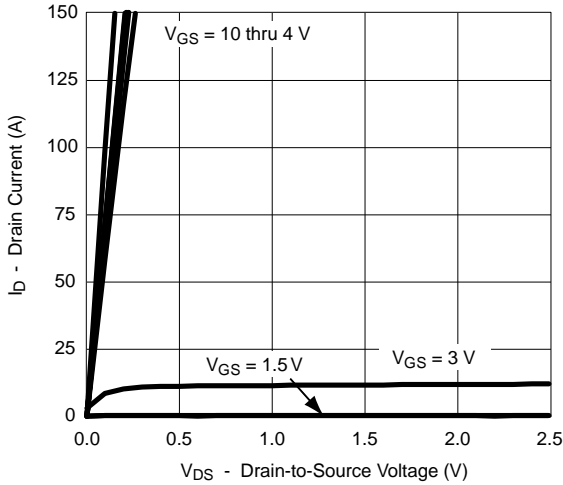
Parameter	Symbol	Test Conditions	Min .	Typ.	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	45			V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$		35		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			- 5.5		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1		3	V
Gate-Source Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 32\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
		$V_{DS} = 32\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			10	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	200			A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 30\text{ A}$		0.0008	0.0012	$\Omega$
		$V_{GS} = 4.5\text{ V}, I_D = 20\text{ A}$		0.0012	0.0016	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 15\text{ V}, I_D = 15\text{ A}$		80		S
<b>Dynamic<sup>b</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		4600		pF
Output Capacitance	$C_{oss}$			3100		
Reverse Transfer Capacitance	$C_{rss}$			105		
Total Gate Charge	$Q_g$	$V_{DS} = 15\text{ V}, V_{GS} = 10\text{ V}, I_D = 20\text{ A}$		110		nC
				59.3		
Gate-Source Charge	$Q_{gs}$	$V_{DS} = 15\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 20\text{ A}$		18		
Gate-Drain Charge	$Q_{gd}$			13		
Gate Resistance	$R_g$	$f = 1\text{ MHz}$		1.4	2.1	$\Omega$
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\text{ V}, R_L = 0.555\text{ }\Omega$ $I_D \cong 30\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$		14	22	ns
Rise Time	$t_r$			10	16	
Turn-Off Delay Time	$t_{d(off)}$			56	85	
Fall Time	$t_f$			10	15	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\text{ V}, R_L = 0.625\text{ }\Omega$ $I_D \cong 20\text{ A}, V_{GEN} = 4.5\text{ V}, R_g = 1\text{ }\Omega$		12	20	
Rise Time	$t_r$			150	220	
Turn-Off Delay Time	$t_{d(off)}$			55	83	
Fall Time	$t_f$			12	18	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Source-Drain Diode Current	$I_S$	$T_C = 25\text{ }^\circ\text{C}$			230	A
Pulse Diode Forward Current <sup>a</sup>	$I_{SM}$				820	
Body Diode Voltage	$V_{SD}$	$I_S = 22\text{ A}$		0.8	1.2	V
Body Diode Reverse Recovery Time	$t_{rr}$	$I_F = 20\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		35	58	ns
Body Diode Reverse Recovery Charge	$Q_{rr}$			90.2	125	nC
Reverse Recovery Fall Time	$t_a$			27		ns
Reverse Recovery Rise Time	$t_b$			25		

Notes:

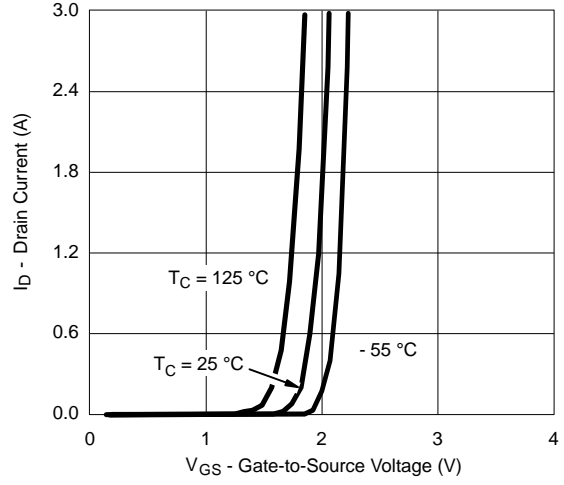
- Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .
- Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

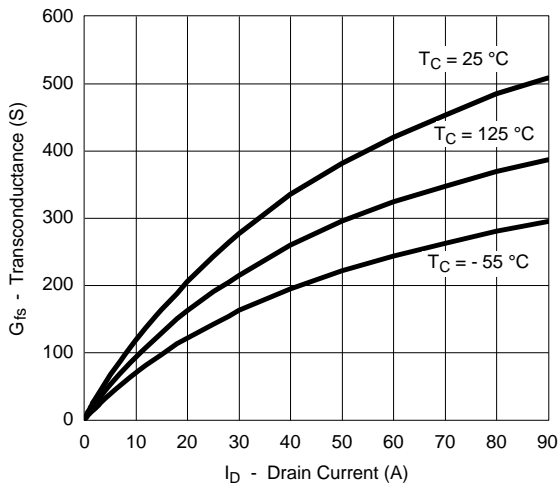
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



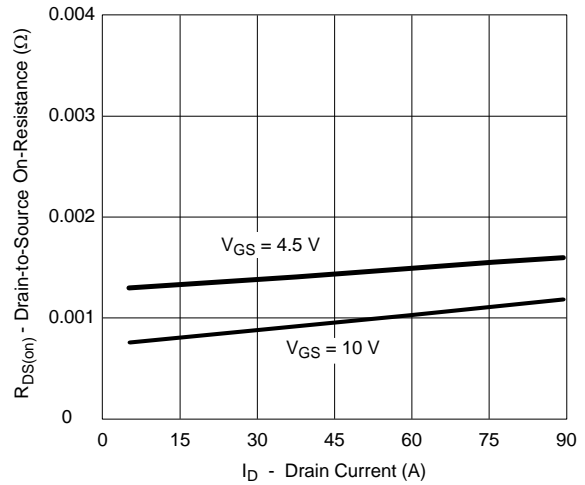
**Output Characteristics**



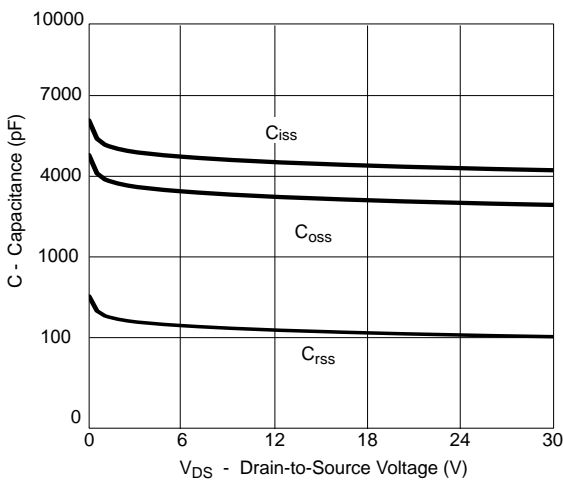
**Transfer Characteristics**



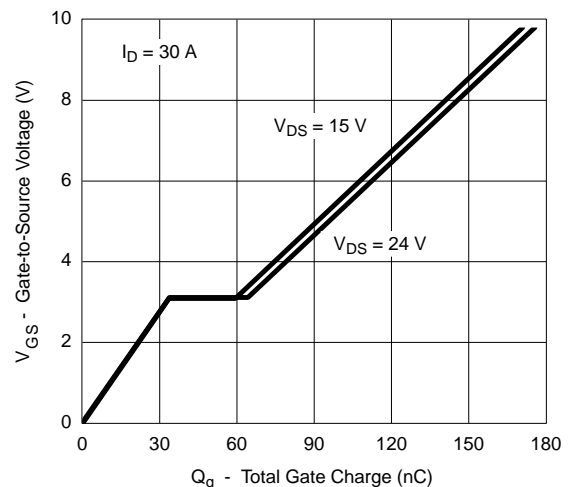
**Transconductance**



**$R_{DS(on)}$  vs. Drain Current**

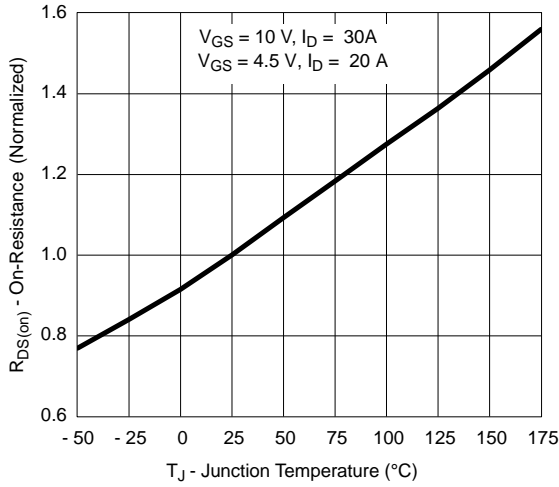


**Capacitance**



**Gate Charge**

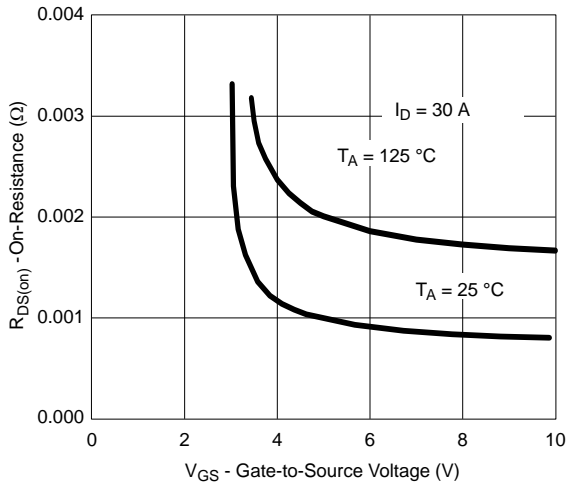
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



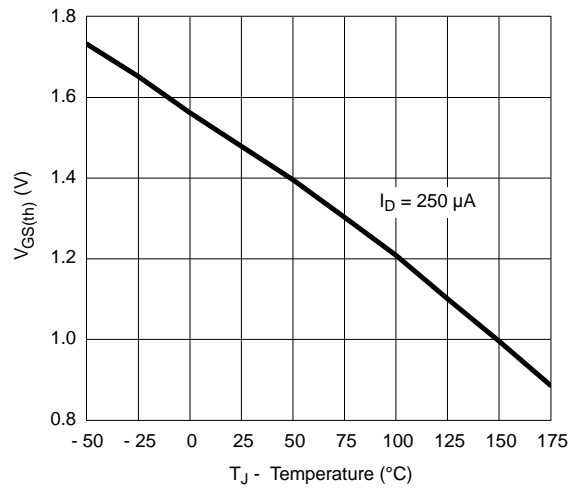
**On-Resistance vs. Junction Temperature**



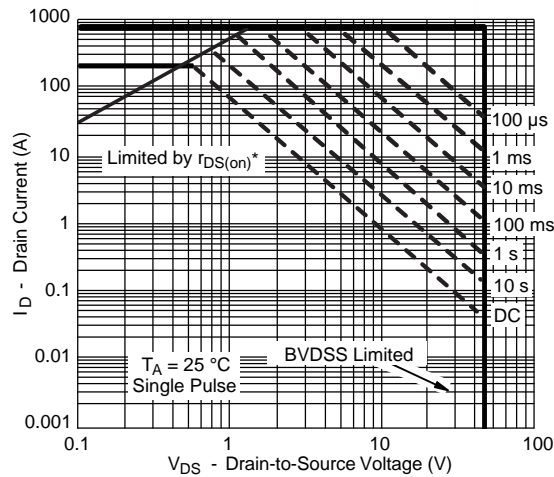
**Forward Diode Voltage vs. Temperature**



**R<sub>DS(on)</sub> vs. V<sub>GS</sub> vs. Temperature**

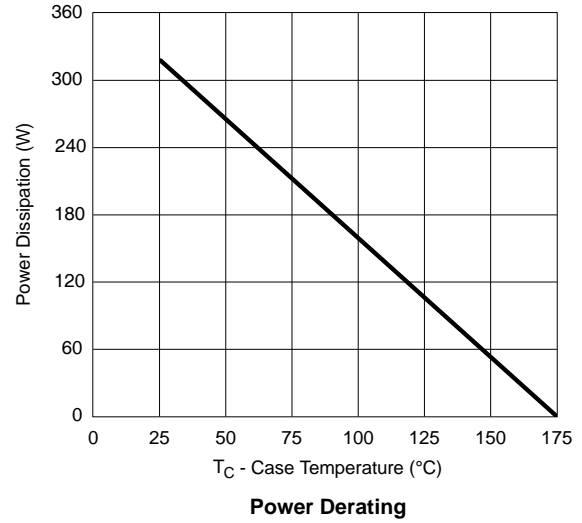
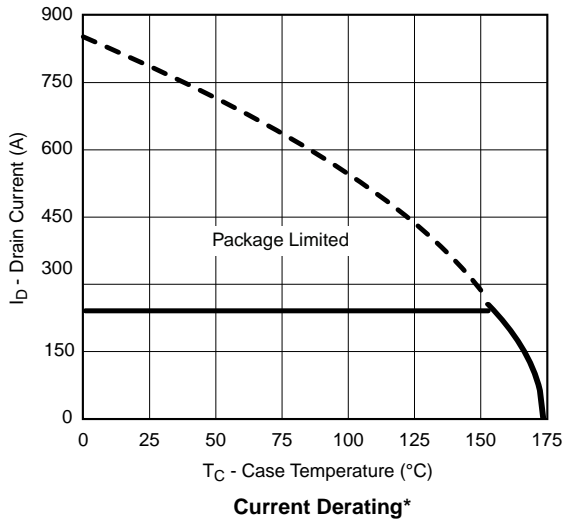


**Threshold Voltage**

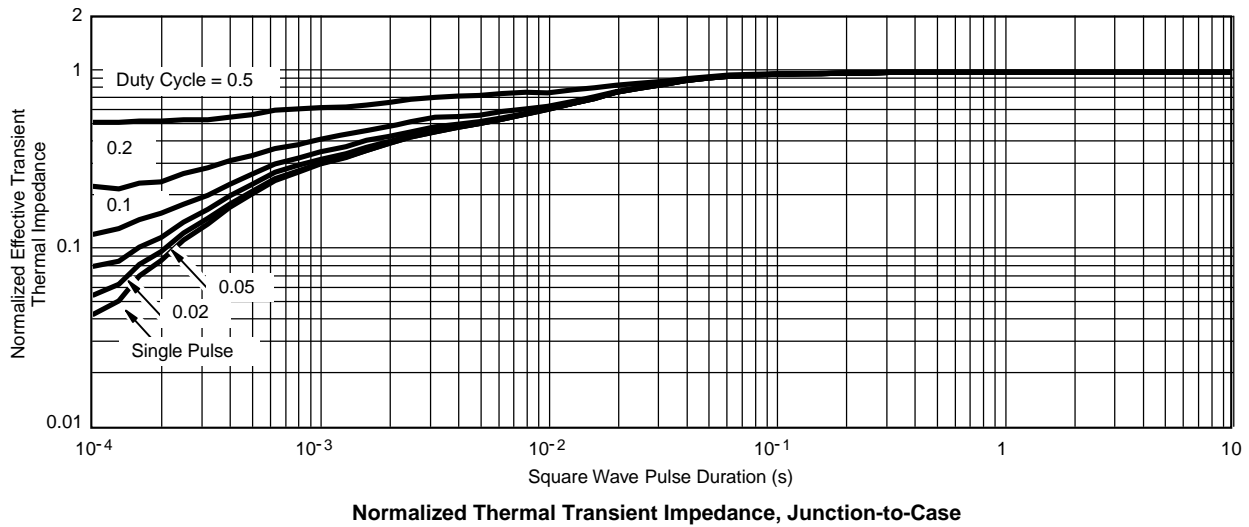


\*V<sub>GS</sub> > minimum V<sub>GS</sub> at which r<sub>DS(on)</sub> is specified  
**Safe Operating Area, Junction-to-Ambient**

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



\* The power dissipation  $P_D$  is based on  $T_{J(max)} = 175$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



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